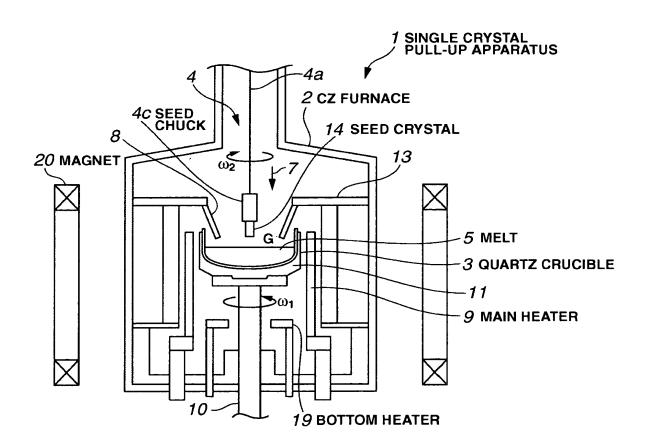
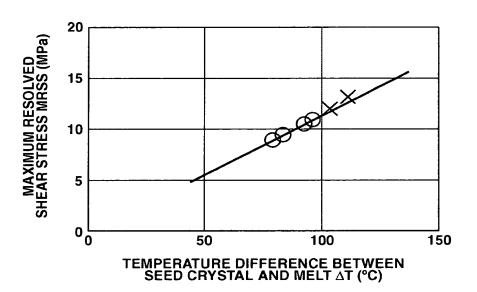
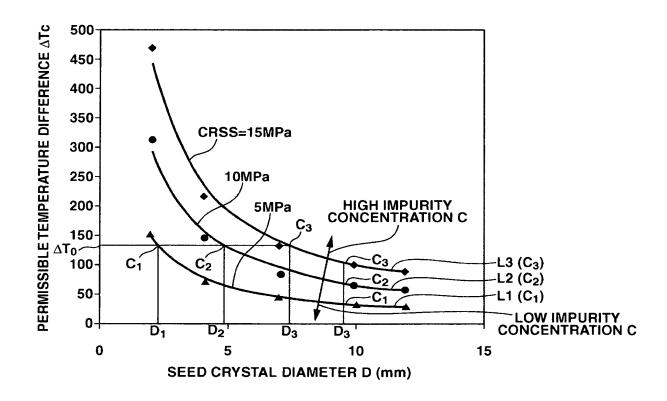
Title: SINGLE CRYSTAL SEMICONDUCTOR MANUFACTURING APPARATUS AND METHOD (Hiroshi Inagaki et al.) Filed: 8/7/2006 Attorney Docket No.: 1110/97936 (SHEET 1 OF 7)



(Hiroshi Inagaki et al.) Filed: 8/7/2006 Attorney Docket No.: 1110/97936 (SF (SHEET 2 OF 7)



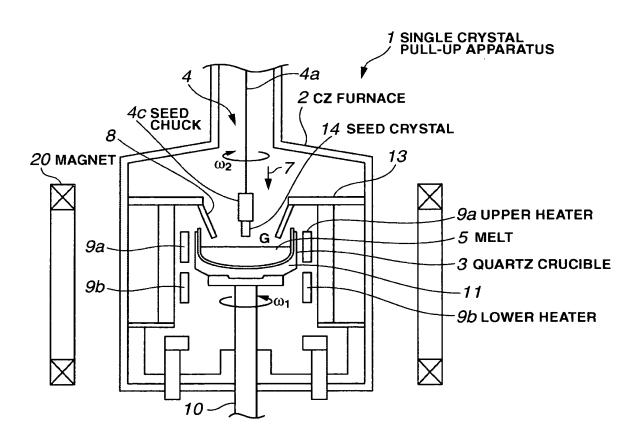
(Hiroshi Inagaki et al.) Filed: 8/7/2006 Attorney Docket No.: 1110/97936 (St (SHEET 3 OF 7)



Title: SINGLE CRYSTAL SEMICONDUCTOR MANUFACTURING APPARATUS AND METHOD (Hiroshi Inagaki et al.) Filed: 8/7/2006 Attorney Docket No.: 1110/97936 (SHEET 4 OF 7)

TEST NO.	(1)	(2)	(3)	(4)	(5)	(9)
MAGNET FIELD STRENGTH (Gauss)	0	0	0	3000	3000	3000
ELECTRIC POWER APPLIED TO BOTTOM HEATER (Kw)	35	10	0	35	10	0
ELECTRIC POWER APPLIED TO MAIN HEATER (Kw)	105	120	138	112	126	143
TEMPERATURE DIFFERENCE BETWEEN SEED CRYSTAL AND MELT ∆T (°C)	111.1	103.2	95.6	92.2	82.5	78.5
RESULT (WITHOUT DISLOCATION: O, WITH DISLOCATION: X)	×	×	0	0	0	0

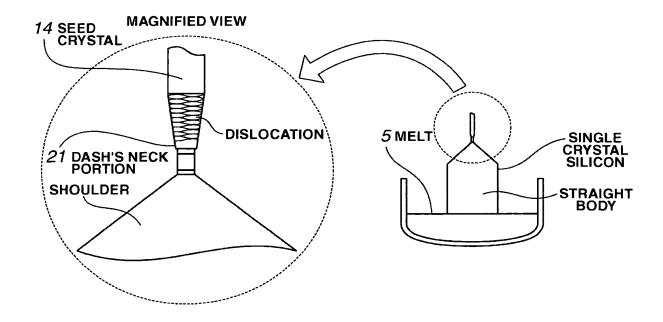
(Hiroshi Inagaki et al.) Filed: 8/7/2006 Attorney Docket No.: 1110/97936 (SI (SHEET 5 OF 7)



(Hiroshi Inagaki et al.) Filed: 8/7/2006 Attorney Docket No.: 1110/97936 (SHEET 6 OF 7)

ELEMENTS	CONCENTRATION (atoms/cc)
В	≧1e18
Ga	≧5e19
In	≧1e16
Р	≧1e19
As	≧5e19
Sb	≧1e19
Ge	≧5e19
N	≧5e13
С	≧8e16

FIG.7



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